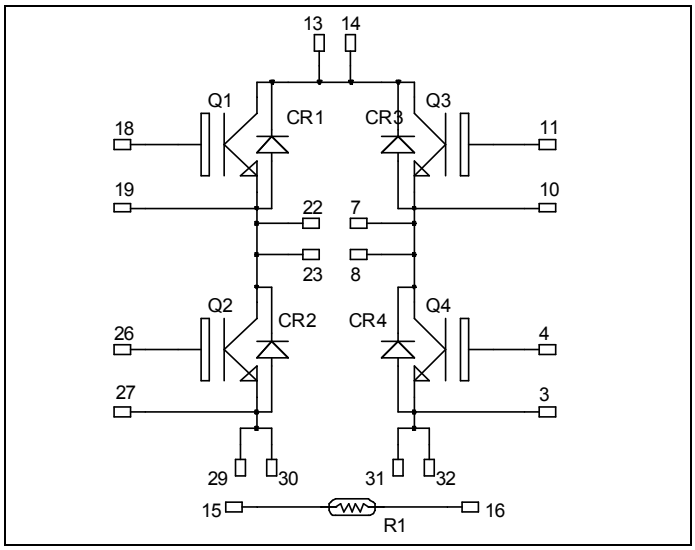
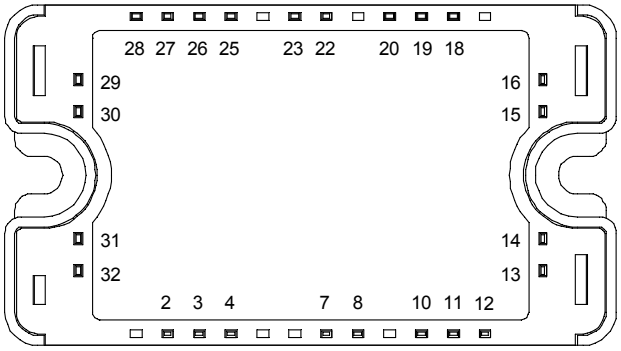
Full - Bridge
NPT IGBT Power Module

V_{CES} = 600V
I_C = 90A @ Tc = 80°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T_C of V_{CEsat}
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	120	A
		T_C = 80°C	90	
I_{CM}	Pulsed Collector Current	T_C = 25°C	315	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	416	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	200A@500V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 600V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$V_{CE(on)}$	Collector Emitter on Voltage	V_{GE} =15V I_C = 100A	T_j = 25°C	1.7	2.0	2.45	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, I_C = 2mA		4		6	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			4400		pF
C_{oes}	Output Capacitance				645		
C_{res}	Reverse Transfer Capacitance				401		
Q_g	Total gate Charge	V_{GE} = 15V V_{Bus} = 300V I_C =100A			331		nC
Q_{ge}	Gate – Emitter Charge				40		
Q_{gc}	Gate – Collector Charge				200		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V V_{Bus} = 400V I_C = 100A R_G = 1.2Ω			40		ns
T_r	Rise Time				9		
$T_{d(off)}$	Turn-off Delay Time				120		
T_f	Fall Time				15		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = 15V V_{Bus} = 400V I_C = 100A R_G = 1.2Ω			42		ns
T_r	Rise Time				10		
$T_{d(off)}$	Turn-off Delay Time				130		
T_f	Fall Time				22		
E_{on}	Turn-on Switching Energy	V_{GE} = 15V V_{Bus} = 400V I_C = 100A R_G = 1.2Ω	T_j = 125°C		1		mJ
E_{off}	Turn-off Switching Energy		T_j = 125°C		2		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 360V t_p ≤ 10µs ; T_j = 125°C			450		A

Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			35	µA
			T_j = 125°C			600	
I_F	DC Forward Current		Tc = 90°C		60		A
V_F	Diode Forward Voltage	I_F = 60A			1.8	2.2	V
		I_F = 120A			2.2		
		I_F = 60A	T_j = 150°C		1.5		
t_{rr}	Reverse Recovery Time	I_F = 60A V_R = 400V di/dt =400A/µs	T_j = 25°C		25		ns
			T_j = 125°C		160		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		70		nC
			T_j = 125°C		960		

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	*Characteristic*		*Min*	*Typ*	*Max*	*Unit*
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
ΔB/B		T_C=100°C		4		%

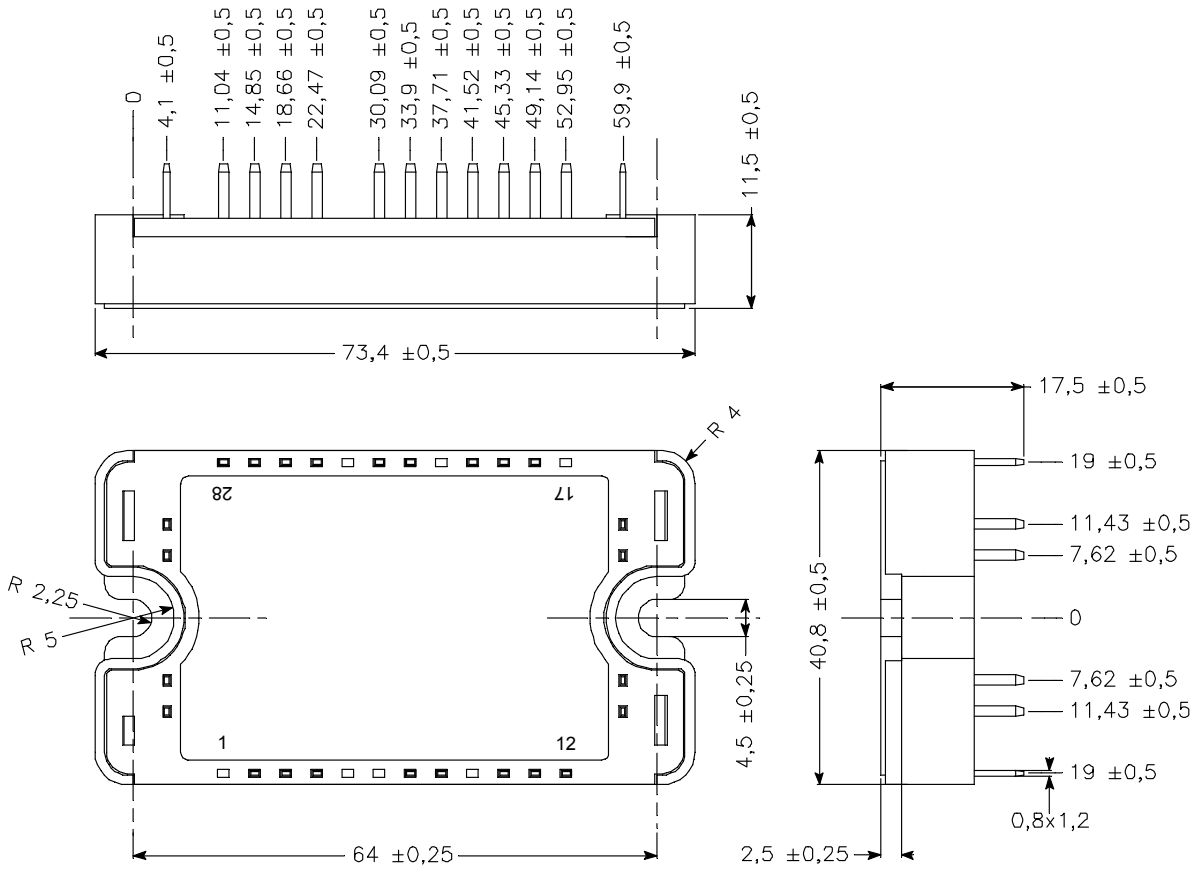
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.3	°C/W
			Diode			0.65	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2.5		4.7	N.m
Wt	Package Weight					110	g

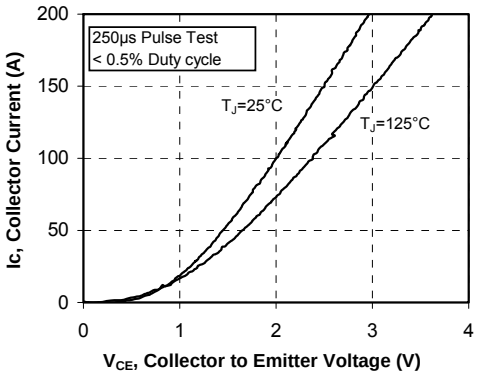
SP3 Package outline (dimensions in mm)



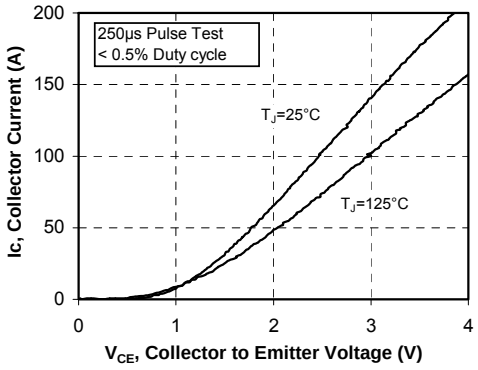
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical IGBT Performance Curve

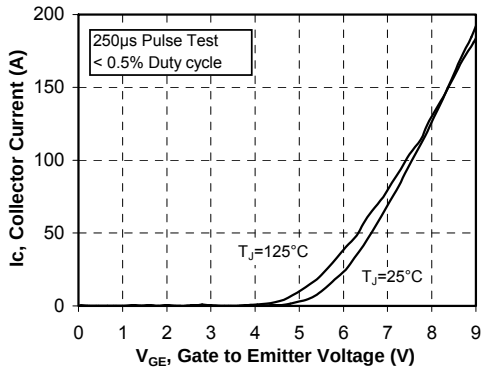
Output characteristics (V_{GE}=15V)



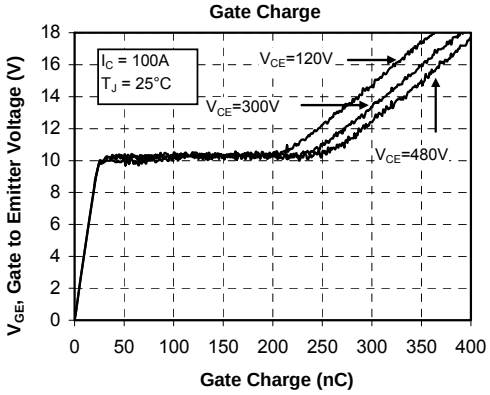
Output Characteristics (V_{GE}=10V)



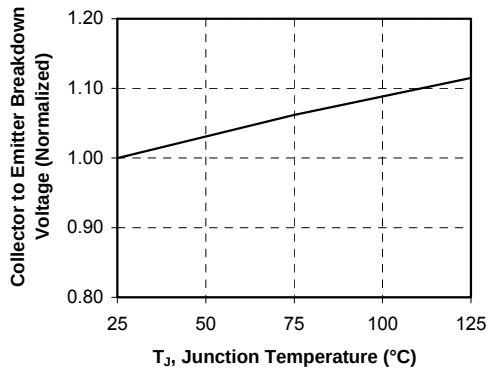
Transfer Characteristics



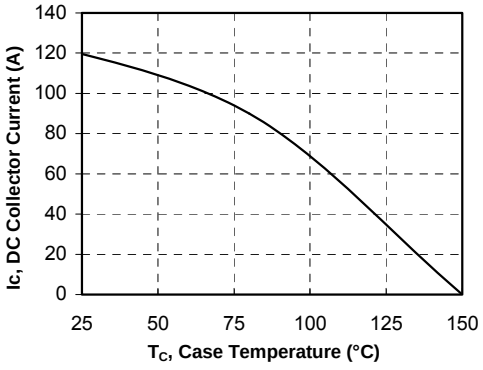
Gate Charge



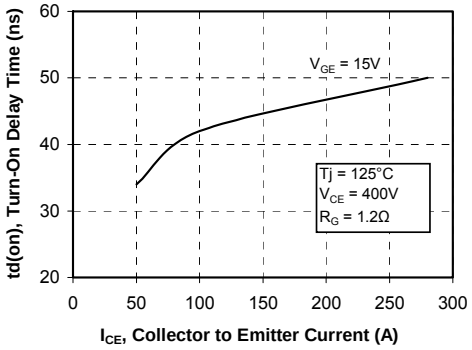
Breakdown Voltage vs Junction Temp.



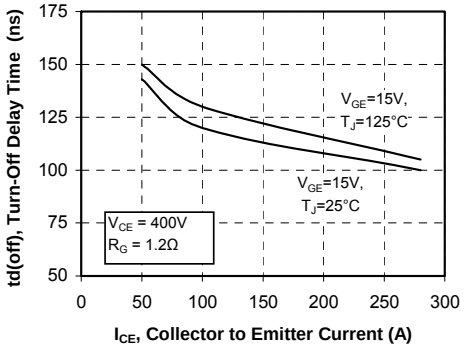
DC Collector Current vs Case Temperature



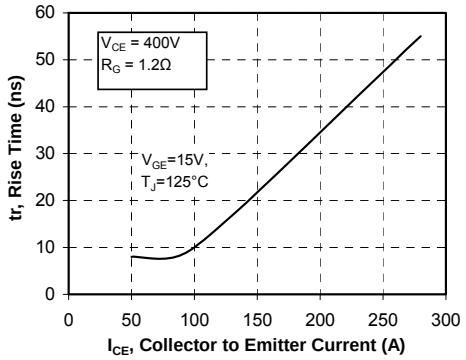
Turn-On Delay Time vs Collector Current



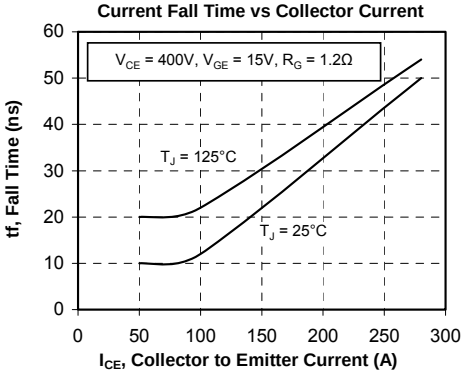
Turn-Off Delay Time vs Collector Current



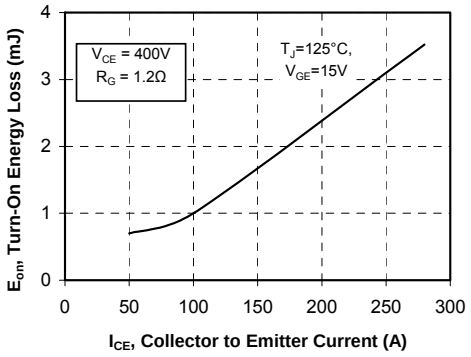
Current Rise Time vs Collector Current



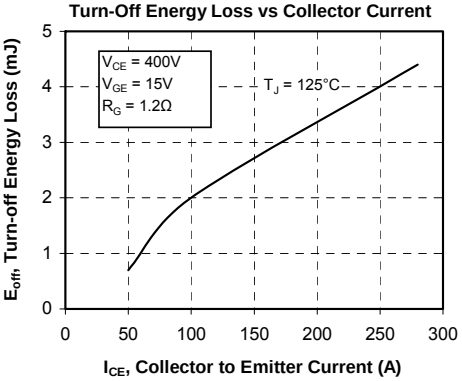
Current Fall Time vs Collector Current



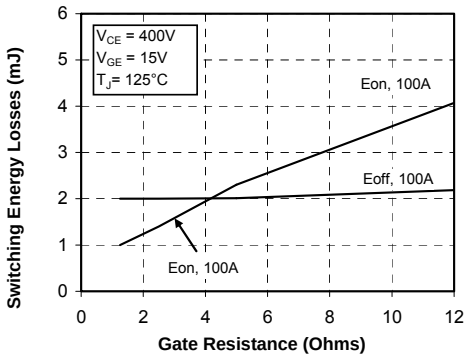
Turn-On Energy Loss vs Collector Current



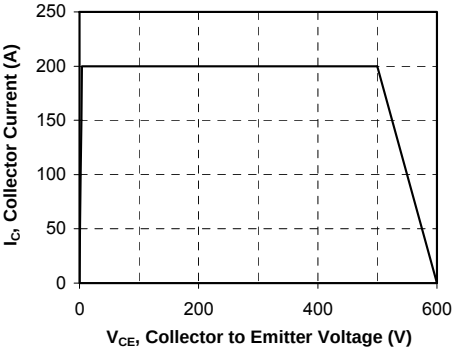
Turn-Off Energy Loss vs Collector Current



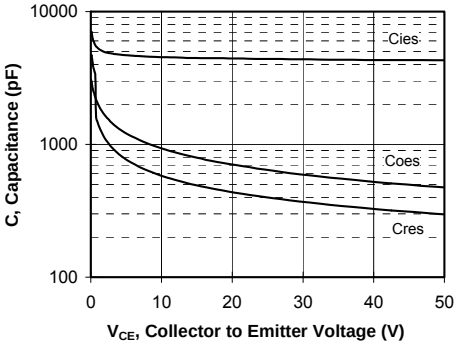
Switching Energy Losses vs Gate Resistance



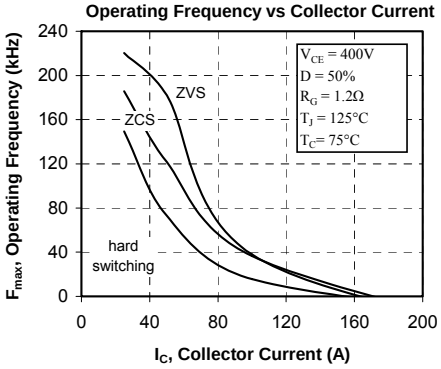
Reverse Bias Safe Operating Area



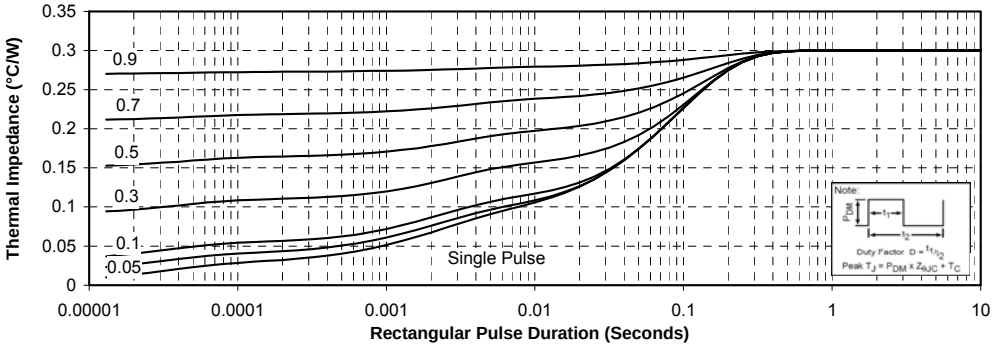
Capacitance vs Collector to Emitter Voltage



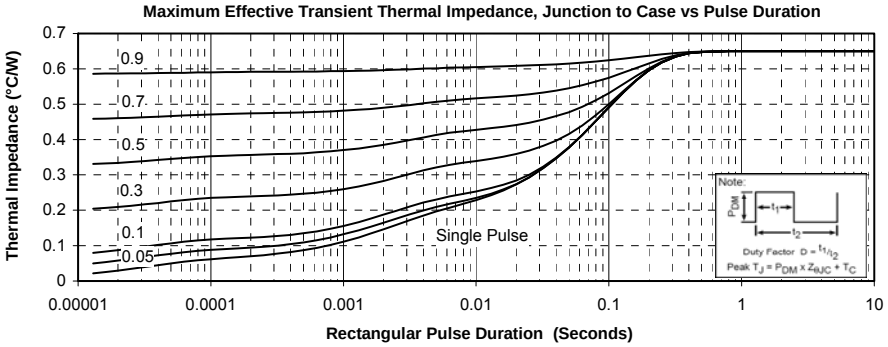
Operating Frequency vs Collector Current

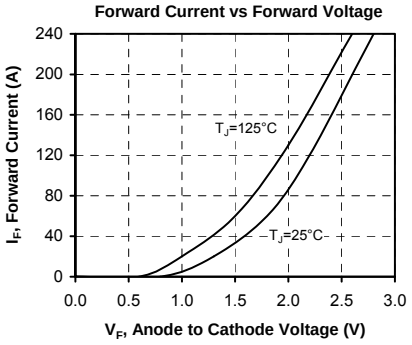


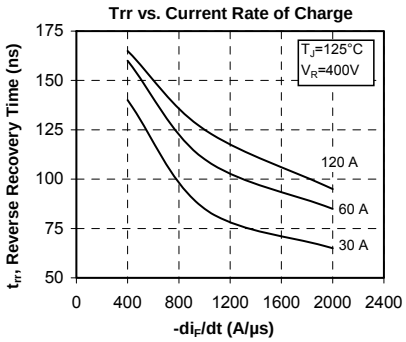
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

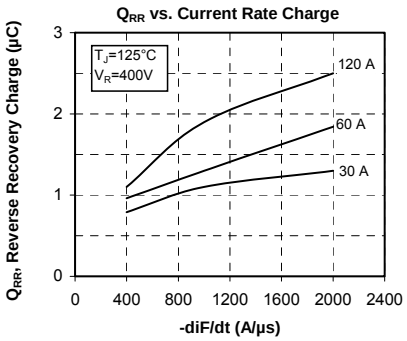


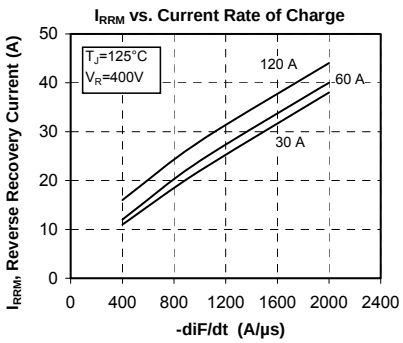
Typical diode Performance Curve

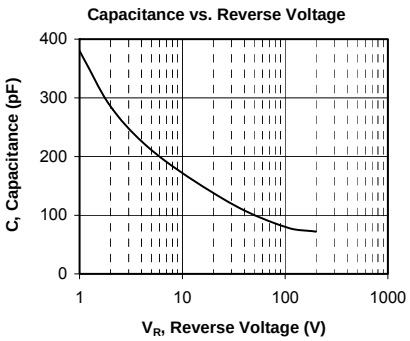


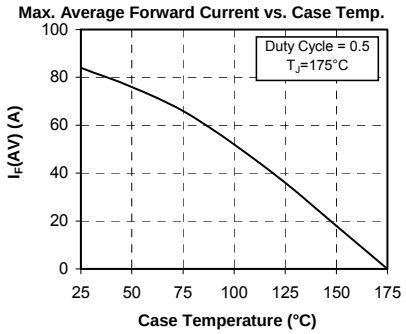












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